Sheet 1 of 2

Form PTO-1449 (Rev. 8-83)

U.S. Department of Commerce Patent and Trademark Office Attorney Docket No. 0756-2218

Serial No. Not Yet Assigned

INFORMATION DISCLOSURE STATEMENT

Applicant: Hongyong ZHANG et al

INFORMATION DISCLOSURE STATEMENT			Applicant: Hongyong ZHANG et al					
_	(Use several sheets if necessa	ry)	Filing Date: October 25, 2000 Group: 281					
		U.S. PATENT	DOCUMENTS					
Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)		
ઘ	4,657,775	04/14/1987	Shiori et al		_			
ધ	5,654,203	11/23/1994	Ohtani et al		-	A PT		
જ	5,808,321	06/07/1994	Mitanaga et al			541 541		
વદ	5,843,225	02/01/1994	Takayama et al	_		0 0 0 0/		
C	5,403,772	04/04/1995	Zhang et al		_	000		
96	4,992,305	02/12/1991	Erbil					
U	5,352,488	10/04/1994	Spencer et al					
90	5.352,631	10/04/1994	Sitaram et al	_				
90	5,147,826	09/15/1992	Liu et al					
al l	5,481,121	01/02/1996	Zhang et al					
વા	5,488,000	01/30/1998	Zhang et al		_	<u></u>		
		FOREIGN PATE	NT DOCUMENTS					
	Document Number	Date	Country	Class	Subclass	Translation Yes		
El	EP 0 174 553 A2	03/19/1986	Europe					
28	61-070716	04/11/1986	Japan			Abstract		
EP	6-029212	02/04/1994	Japan			Abstract		
50	2-140915	05/30/1990	Japan	437	40TFT			
28	63-155714	06/28/1988	Japan		· 11504.5			
El 21	61-63017	04/01/1986	Japan					
20	2-222546	09/05/1990	Japan					
25	5-90518	04/09/1993	Japan	<u> </u>				
	OTHER DOCU	MENTS (Including A	Author, Title, Date, Pertin	ent Pages,	Etc.)			
80	F. Spaepen et al., Crucial Growth of Si"	issues in Semic. N	flat. & Proc. Technol	l., S. Coff	a et al., eds, N	letal-enhanced		
EP	J.E. Greene et al., Thin Solid Films 34 (1976) 27, "Metal induced crystallization of R.F. sputtered a Sifilms"							
	ASM Handbook, Vol. 5, p5	10-531 (1994)						
Examiner	iner Eugn Pert Date Considered 5/21/0/							
	Initial if citation considered	. whether or not c		nance wit	h MPEP 609; [raw line throu		

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO-1449 U.S. Department of Commerce Attorney Docket No. 0756-2218 Serial No. Not Yet Assigned (Rev. 8-83) Patent and Trademark Office Applicant: Hongyong ZHANG et al INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary) Filing Date: October 25, 2000 Group: 2813 ≣ທ **U.S. PATENT DOCUMENTS** Examiner **Document Number** Date Name Class **Subclass** Filing Date Initial (if appropriate) 5,147,826 09/15/1992 Liu et al 437 233 ٤ 4,796,083 01/03/1989 Cherukuvi et al 01/04/1994 5,275,851 Fonash et al 437 233 03/03/1993 5,264,383 11/23/1993 Young 437 40TFT 41 5,403,772 04/04/1995 Zhang et al 437 101 12/03/1993 5,426,064 06/20/1995 Zhang et al 437 40TFT 03/08/1994 FOREIGN PATENT DOCUMENTS **Document Number** Date **Subclass** Country Class **Translation** Yes No OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) G. Radnoczi et al., J. Appl. Phys., 69(9) (1991) 6394, "Al induced crystallization of a Si" ટી A.V. Dvurechenskii et al., "Transport Phenomena in Amorphous Silicon Doped by Ion Implanataion of 3rd Metals", Akademikian Lavrentec Propsekt 13, 630090 Novosibrisk 90, USSR, pp. 635-640 T. Hempel, et al. Solid State Comm., 85,11(1993)921 "Needle-Like Crystallization of Ni Doped A-Si Thin Films" Sl J.R. Bosnell, et al., Thin Solid Films, 6(1970) 161 "...The Influence of Contact Materials or ... Crystallization..." 21 C. Hayzelden et al., Appl. Phys. Lett., 60,2(1992)225 "...TEM Studies of Silicide Mediated Crystallization..." Y.N. Efokhin, et al., Appl. Phys. Lett., 63,23(1993) 3173 "... NiSiz Formation ... on Preamorphized Silicon 1 T.T. Ngo, et al., Appl. Phys. Left. 66,15(1995) 1906-1908 "... Growth of Monodisperse Islands" 21 28 Y. Kawazu et al., Jpn. J. Appl. Phys., 29,12(1990)2698 "...Crystallization of A-Si:H Induced by Nickel..." D. Tonneau et al., J. de Physique, coll. C5, 5,50(1989)647 "...Metal Carbonyis for CVD of Microstrues" EP S. Wolfe & R.N. Tavber, "Silicon Processing got the VLSI Era" Vol I, 1986, P. 51-3, 335 **Examiner Date Considered** *EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through

citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Please type	a plus	sign (+)	insid.	iis box –
-------------	--------	----------	--------	-----------

DEC 0 2 2002

#13 PTO/SB/08A (08-00)

Approved for use through 10/31/2002. OMB 0651-0031 Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

US Patent and Trademark Office: U.S. DEPARTMENT OF COMM nder the Paperwork Reduction Act of 1995, no personare required to respond to collection of information unless it contains a valid OMB control number.

Substitute	for form 1449A/PTO		E. Carpa	DEMARK	Complete if Known
INEO	DMATIONI	NEC		Application Number	09/695,414
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Filing Date	October 25, 2000
				First Named Inventor	Hongyong ZHANG et al.
				Group Art Unit	2829
				Examiner Name	E. Pert
Sheet	1	of	1	Attorney Docket Number	0756-2218

		·		U.S. PATENT DOCUMENT	rs	
Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited	Date of Publication of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)	Document	MM-DD-YYYY	
EP		5,861,337		Zhang et al.	01/19/1999	
श्र		6,174,374	B1	Zhang et al.	01/16/2001	
<u> </u>		5,352,291		Zhang et al.	10/04/1994	
46		5,578,520		Zhang et al.	11/26/1996	
<i>-</i>						

				F	OREIGN PATENT DOC	UMENTS			
Examiner Initials*	Cite No. ¹	Office ³	Foreign Patent D Number ⁴	ocument Kind Code ⁵ (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶	
				TUED PRIOR	ADT NON DATEST ITE	DATURE DOCUMENTS			
				THER PRIOR	ART – NON PATENT LITE	RATURE DUCUMENTS		1	
Examiner Initials	Cite No.1			clude name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the n (book, magazine, journal, serial, symposium, catalog, etc.)., date, page(s), volume-issue number(s), publisher, city and/or country where published.					
		+	<u>.</u>						
		-							

Examiner Signature	Zent	Date Considered	2/	19/03
Digitature		Complete		

^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, Washington, DC 20231.

¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

¹Unique citation designation number. ² Applicant is to place a check mark here if English language Translation is attached.